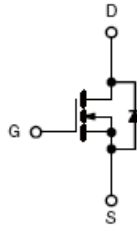


:95HI F9`

TrenchFET Power MOSFET

5DD@=7 5H-CBG`

- Load Switch for Portable Devices
- DC/DC Converter



9e i]jU`Ybh` 7]fWi]h`



AUI]a i a `fUh]b [g`flH₀1&)°C` i b`Ygg`ch\Yfk]gY`bchYXL`

DUfU a YhYf`	Gma Vcl	JU` i Y	I b]h
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	
Continuous Drain Current	I_D	4.0	A
Continuous Source-Drain Current(Diode Conduction)	I_S	0.6	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient (tm5s)	R_{JA}	357	°C/W
Operating Junction	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~+150	

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 10μA	20			V
Gate-threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 50μA	0.5	0.95	1.25	
Gate-body leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	μA
Drain-source on-resistance ^a	r _{DS(on)}	V _{GS} = 4.5V, I _D = 4.0A		0.021	0.027	δ
		V _{GS} = 2.5V, I _D = 3.0A		0.029	0.037	
Forward transconductance ^a	g _{fs}	V _{DS} = 5V, I _D = 3.6A		8		S
Diode forward voltage	V _{SD}	I _S = 0.94A, V _{GS} = 0V		0.76	1.2	V
Dynamic						
Total gate charge	Q _g	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3.6A		4.0		nC
Gate-source charge	Q _{gs}			0.65		
Gate-drain charge	Q _{gd}			1.5		
Input capacitance ^b	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		300		pF
Output capacitance ^b	C _{oss}			120		
Reverse transfer capacitance ^b	C _{rss}			80		
Switching^b						
Turn-on delay time	t _{d(on)}	V _{DD} = 10V, R _L = 5.5 Ω, I _D = 3.6A, V _{GEN} = 4.5V, R _g = 6Ω		7		ns
Rise time	t _r			55		
Turn-off delay time	t _{d(off)}			16		
Fall time	t _f			10		

Notes :

- Pulse Test : Pulse width 300μs, duty cycle 2%.
- These parameters have no way to verify.

Hmd]WU`7 \UfUWhYf]gh]Wg

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